



#### **DUAL N-CHANNEL ENHANCEMENT MODE MOSFET**

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> T <sub>A</sub> = +25°C
20V	$13m\Omega @ V_{GS} = 4.5V$	9.0A
	$14m\Omega @ V_{GS} = 4.0V$	8.7A
	$17m\Omega @ V_{GS} = 3.1V$	8.0A
	$18m\Omega @ V_{GS} = 2.5V$	6.7A
	$28m\Omega$ @ $V_{GS} = 1.8V$	6.3A

### **Description**

This new generation MOSFET has been designed to minimize the onstate resistance  $(R_{DS(ON)})$  and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

### **Applications**

- Power Management Functions
- Battery Pack
- Load Switch

#### **Features**

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: U-DFN2030-6 (Type B)
- Case Material: Molded Plastic, "Green" Molding Compound UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Weight: 0.012 grams (Approximate)

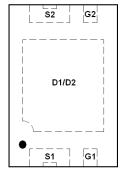


ESD PROTECTED TO 2kV

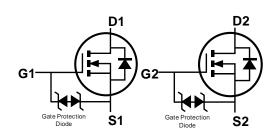




**Bottom View** 



Top View



**Equivalent Circuit** 

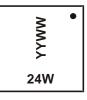
### Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2014LHAB-7	U-DFN2030-6 (Type B)	3,000 / Tape & Reel
DMN2014LHAB-13	U-DFN2030-6 (Type B)	10,000 / Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

### Marking Information



24W = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 16 for 2016) WW = Week code (01 to 53)

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Characte	Symbol	Value	Unit		
Drain-Source Voltage	$V_{DSS}$	20	V		
Gate-Source Voltage	V <sub>GSS</sub>	±12	V		
Continuous Drain Current (Note 6) V <sub>GS</sub> = 4.5V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I <sub>D</sub>	9.0 7.1	Α
	t < 10s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I <sub>D</sub>	9.3 7.4	А
Pulsed Drain Current (10µs Pulse, Duty Cycle =	I <sub>DM</sub>	45	А		

## **Thermal Characteristics**

Characteristic	Symbol	Value	Units		
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	C	0.8	W	
Total Fower Dissipation (Note 5)	$T_A = +70^{\circ}C$	$P_{D}$	0.5		
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	D	157	°C/W	
Thermal Resistance, Junction to Ambient (Note 3)	t < 10s	$R_{\theta JA}$	148		
Total Power Dissipation (Note 6)	$T_A = +25^{\circ}C$	D-	1.7	W	
Total Fower Dissipation (Note 0)	$T_A = +70^{\circ}C$	$P_{D}$	1.1	VV	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	D	73.7		
Thermal Resistance, Junction to Ambient (Note o)	t < 10s	$R_{\theta JA}$	68	°C/W	
Thermal Resistance, Junction to Case		$R_{ heta JC}$	9.4		
Operating and Storage Temperature Range		$T_{J_i}T_{STG}$	-55 to +150	°C	

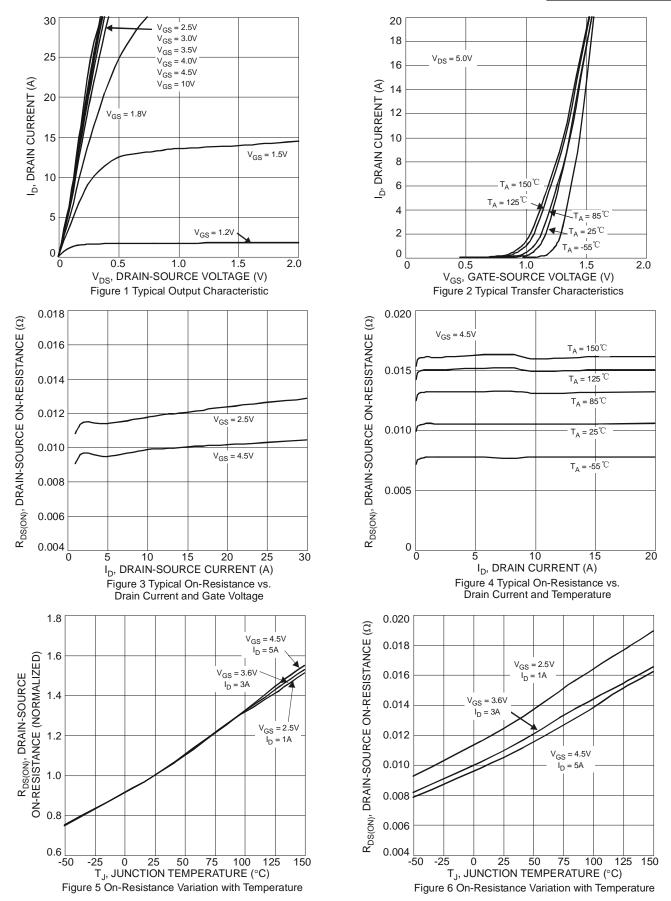
## **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	l	l	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>			1.0	μΑ	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-Source Leakage	$I_{GSS}$	1	1	±10	μΑ	$V_{GS} = \pm 8V$ , $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)	ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.3	0.71	1.1	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
			10	13	mΩ	$V_{GS} = 4.5V, I_D = 4.0A$	
			11	14		$V_{GS} = 4.0V, I_D = 4.0A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	12	17		$V_{GS} = 3.1V$ , $I_D = 4.0A$	
			13	18		$V_{GS} = 2.5V, I_D = 4.0A$	
			19	28		$V_{GS} = 1.8V, I_D = 3.5A$	
Forward Transfer Admittance	Y <sub>fs</sub>		25		S	$V_{DS} = 5V, I_{D} = 6A$	
Diode Forward Voltage	$V_{SD}$		0.75	1.0	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 8)						_	
Input Capacitance	C <sub>iss</sub>	_	1550	_	pF	1/ 101/1/ 01/	
Output Capacitance	Coss		166		pF	$V_{DS} = 10V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	1	145	l	рF	1 – 1.0101112	
Gate Resistance	$R_g$		1.37	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 2.5V)	Qg	_	8.4	_	nC		
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	_	16	_	nC	V <sub>DS</sub> = 10V, I <sub>D</sub> = 6A	
Gate-Source Charge	$Q_{gs}$	_	2.3	_	nC		
Gate-Drain Charge	$Q_{gd}$	_	2.5	_	nC		
Turn-On Delay Time	t <sub>D(ON)</sub>	_	6.9	_	ns		
Turn-On Rise Time	t <sub>R</sub>	_	15.5	_	ns	$V_{DD} = 10V, R_{L} = 1.7\Omega,$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	40.9	_	ns	$V_{GS} = 5.0V$ , $R_g = 3\Omega$	
Turn-Off Fall Time	t <sub>F</sub>	_	12	_	ns	1	

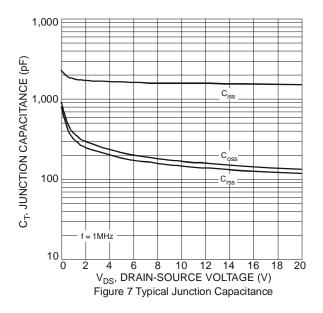
 Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout
 Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad
 Repetitive rating, pulse width limited by junction temperature
 Guaranteed by design. Not subject to product testing Notes:

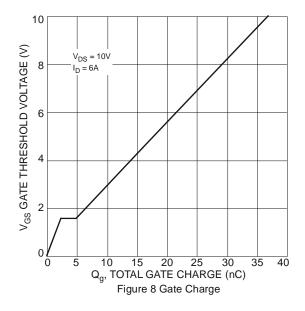
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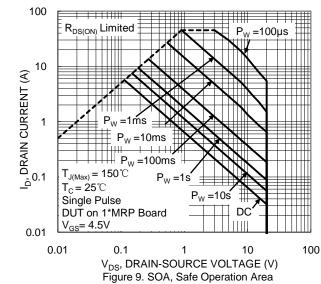


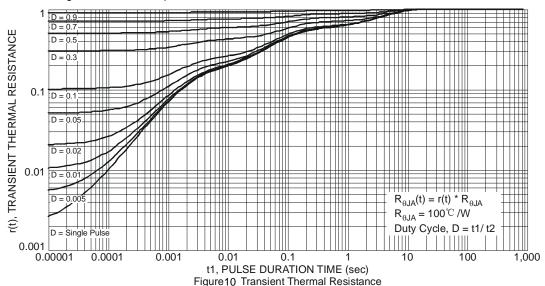










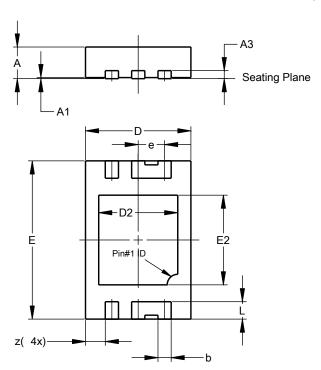




### **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### U-DFN2030-6 (Type B)

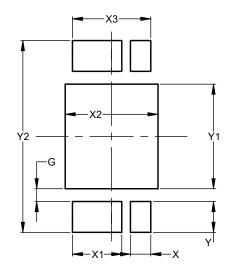


U-DFN2030-6					
(Type B)					
Dim	Min	Max	Тур		
Α	0.55	0.65	0.60		
A1	0.00	0.05	0.02		
A3		1	0.15		
b	0.20	0.30	0.25		
D	1.95	2.05	2.00		
D2	1.40	1.60	1.50		
Е	2.95	3.05	3.00		
E2	1.65	1.75	1.70		
е		1	0.50		
L	0.28	0.38	0.33		
Z		-	0.375		
All Dimensions in mm					

### **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### U-DFN2030-6 (Type B)



Dimensions	Value		
Dilliensions	(in mm)		
G	0.220		
Х	0.350		
X1	0.850		
X2	1.600		
Х3	1.350		
Y	0.530		
Y1	1.800		
Y2	3.300		



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